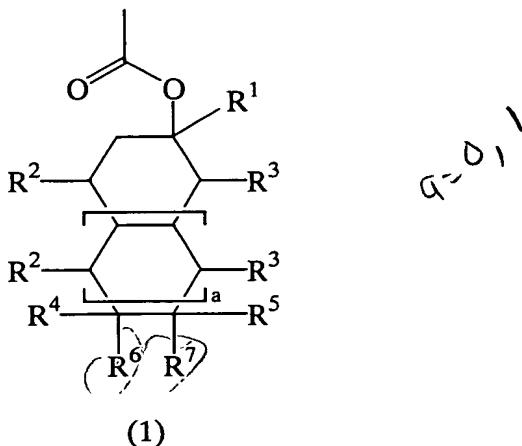


CLAIMS:

1. A polymer containing a group of the following general formula (1) and having a weight average molecular weight of
5 1,000 to 500,000,

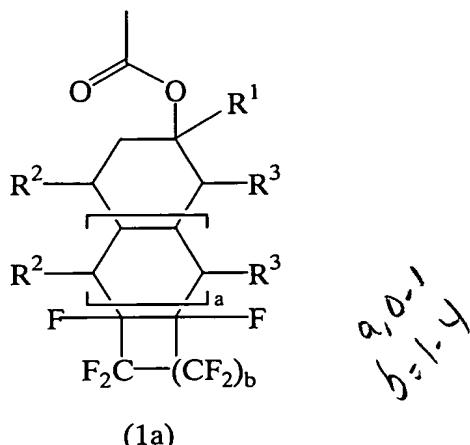


wherein R¹ to R³ each are hydrogen, fluorine or a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 10 20 carbon atoms, R² and R³ may bond together to form a ring and in that event, each is an alkylene group of 1 to 20 carbon atoms which may contain a hetero atom such as oxygen, sulfur or nitrogen,

R⁴ and R⁵ each are hydrogen or fluorine,
R⁶ and R⁷ each are hydrogen, fluorine or a straight, 15 branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms, at least one of R⁶ and R⁷ contains at least one fluorine atom, R⁶ and R⁷ may bond together to form a ring and in that event, each is a straight, branched or cyclic alkylene or fluorinated alkylene group of 1 to 20 carbon atoms, and

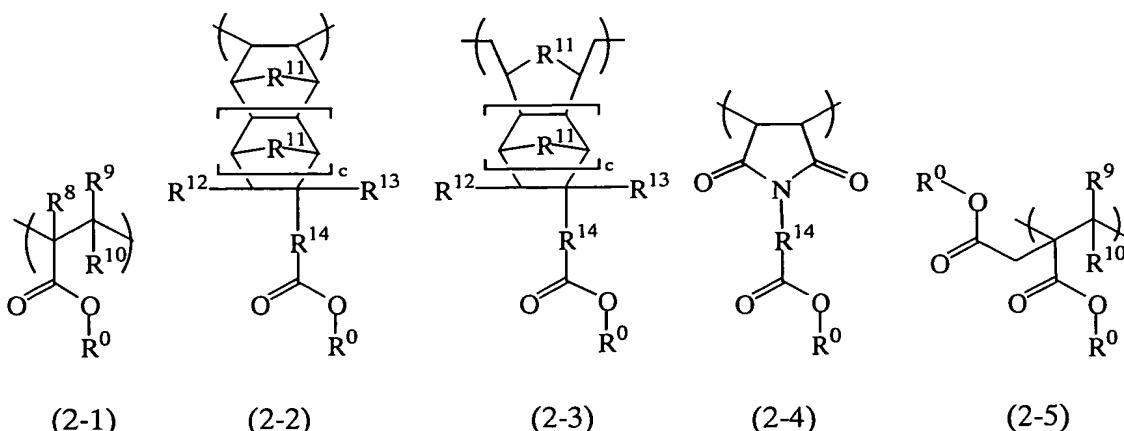
"a" is 0 or 1.

2. The polymer of claim 1 containing a group of the following general formula (1a):



wherein R¹ to R³ each are hydrogen, fluorine or a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms, R² and R³ may bond together to form a ring and in that event, each is an alkylene group of 1 to 20 carbon atoms which may contain a hetero atom such as oxygen, sulfur or nitrogen, "a" is 0 or 1, and "b" is an integer of 1 to 4.

3. The polymer of claim 1 having a partial structure of any one of the following general formulae (2-1) to (2-5):



wherein R⁰ is a group of formula (1) in claim 1 or a group of formula (1a) in claim 2,

R⁸ to R¹⁰ each are hydrogen, fluorine or a straight, branched or cyclic alkyl or fluorinated alkyl group of 1 to 20 carbon atoms,

5 R¹¹ is a methylene group, oxygen atom or sulfur atom,
R¹² and R¹³ each are hydrogen, methyl or CH₂CO₂R¹⁵,

R¹⁴ is a straight, branched or cyclic alkylene or fluorinated alkylene group of 1 to 20 carbon atoms,

10 R¹⁵ is a straight, branched or cyclic alkyl or substituted alkyl group of 1 to 20 carbon atoms, and

"c" is 0 or 1.

4. A resist composition comprising the polymer of claim 1.

Sub
X
5 15 5. A chemically amplified, positive resist composition comprising

(A) the polymer of any one of claims 1 to 3,
(B) an organic solvent, and
(C) a photoacid generator.

20 6. The resist composition of claim 5 further comprising
(D) a basic compound.

7. The resist composition of claim 5 further comprising
(E) a dissolution inhibitor.

25 8. A process for forming a resist pattern comprising the steps of:

applying the resist composition of claim 4 onto a substrate to form a coating,

30 heat treating the coating and then exposing it to high-energy radiation in a wavelength band of 100 to 180 nm or 1 to 30 nm through a photo mask, and

optionally heat treating the exposed coating and developing it with a developer.

9. The pattern forming process of claim 8 wherein the high-energy radiation is an F₂ laser beam, Ar₂ laser beam or soft x-ray.